

point at which the ion energy does not contribute to etching to a stage on which a sample is placed independently of the generation of the plasma; and

on-off modulating the rf bias voltage to which a peak to peak voltage Vpp value larger than a Vpp value of a continuous rf bias voltage at which the same etch rate can be obtained is given.

2. (amended) A method according to claim 1, wherein the frequency of the rf bias voltage is set to a range from about 100k Hz to a few MHz and the Vpp value of the rf bias voltage is set to 500V or higher.

Please cancel claim 3 without prejudice or disclaimer of the subject matter thereof, and add the following new claim:

--29. A method according to claim 1, wherein the ion energy distribution is a saddle-shaped ion energy distribution.--

#### REMARKS

By the above amendment, claim 1 has been amended to clarify features of the present invention and, in particular, to recite the feature of applying an rf bias voltage of a frequency sufficient to form an ion energy distribution including a high peak point at which the ion energy has high